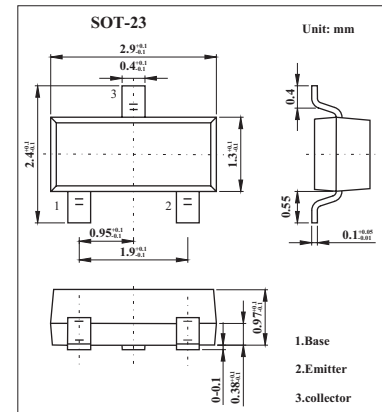


NPN Medium Frequency Transistor

BFS19

■ Features

- Low current (max. 30 mA)
- Low Voltage (max. 20 V)

■ Absolute Maximum Ratings $T_A=25^\circ\text{C}$

Parameter	Symbol	Max	Unit
Collector-base voltage (Emitter open)	V_{CB0}	30	V
Collector-emitter voltage (Base open)	V_{CEO}	20	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	30	mA
Peak collector current	I_{CM}	30	mA
Total power dissipation	P_{tot}	250	mW
Storage temperature	T_{stg}	150	$^\circ\text{C}$
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	T_{amb}	150	$^\circ\text{C}$

■ Electrical Characteristics $T_A=25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base Breakdown voltage	BV_{CB0}	$I_C = 100 \mu\text{A}, I_E = 0$	30			V
Collector-emitter Breakdown voltage	BV_{CEO}	$I_C = 1\text{mA}, I_B = 0$	20			V
Emitter-base Breakdown voltage	BV_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current	I_{CB0}	$V_{CB} = 20\text{V}, I_E = 0$ $V_{CB} = 20\text{V}, I_E = 0, T_j = 100^\circ\text{C}$			100 10	nA μA
Emitter-base cutoff current	I_{EBO}	$V_{EB} = 5.0\text{V}, I_C = 0$			100	nA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}$	65		225	
Emitter-base voltage	V_{BE}	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}$	650		740	mV
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 1\text{mA}, f = 100\text{MHz}$		260		MHz
Collector capacitance	C_C	$V_{CB} = 10\text{V}, I_E = 1\text{mA}, f = 1\text{MHz}$		1		pF
Feedback capacitance	C_{re}	$V_{CB} = 10\text{V}, I_C = 0\text{mA}, f = 1\text{MHz}$		0.85		pF

■ Marking

Marking	F2
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